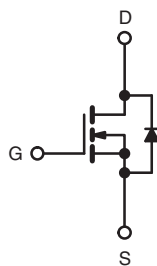
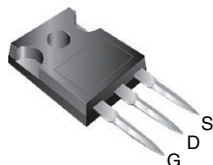


Power MOSFET

TO-247


N-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Isolated central mounting hole
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION

Package	TO-247
Lead (Pb)-free	IRFP460PbF

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	500	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	$T_C = 25\text{ }^{\circ}\text{C}$	A
		$T_C = 100\text{ }^{\circ}\text{C}$	
Pulsed drain current ^a	I_{DM}	80	
Linear derating factor		2.2	W/ $^{\circ}\text{C}$
Single pulse avalanche energy ^b	E_{AS}	960	mJ
Repetitive avalanche current ^a	I_{AR}	20	A
Repetitive avalanche energy ^a	E_{AR}	28	mJ
Maximum power dissipation	P_D	280	W
Peak diode recovery dV/dt ^c	dV/dt	3.5	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Soldering recommendations (peak temperature)	for 10 s	300 ^d	
Mounting Torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 4.3\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 20\text{ A}$ (see fig. 12)
- $I_{SD} \leq 20\text{ A}$, $dI/dt \leq 160\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$
- 1.6 mm from case

THERMAL RESISTANCE RATINGS

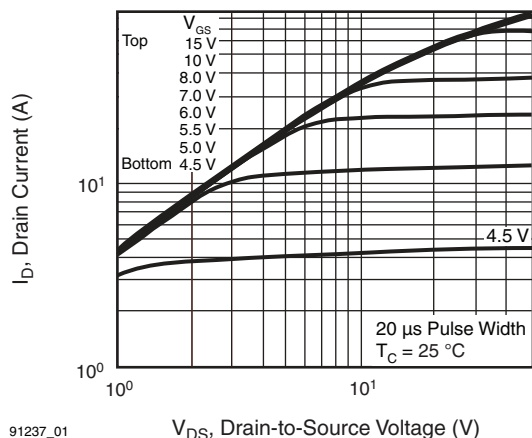
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.24	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.45	

SPECIFICATIONS $T_J = 25\text{ °C}$, unless otherwise noted

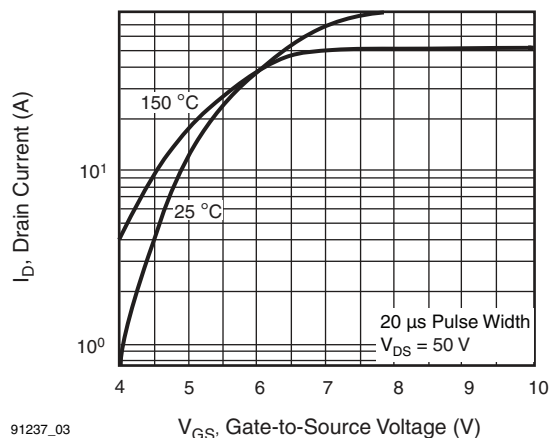
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		500	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.63	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 12 A ^b	-	-	0.27	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 12 A ^b		13	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	4200	-	pF
Output capacitance	C _{oss}			-	870	-	
Reverse transfer capacitance	C _{rss}			-	350	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 20 A, V _{DS} = 400 V see fig. 6 and 13 ^b	-	-	210	nC
Gate-source charge	Q _{gs}			-	-	29	
Gate-drain charge	Q _{gd}			-	-	110	
Turn-on delay time	t _{d(on)}	V _{DD} = 250 V, I _D = 20 A , R _G = 4.3 Ω, R _D = 13 Ω, see fig. 10 ^b		-	18	-	ns
Rise time	t _r			-	59	-	
Turn-off delay time	t _{d(off)}			-	110	-	
Fall time	t _f			-	58	-	
Internal drain inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	5.0	-	nH
Internal source inductance	L _S			-	13	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	20	A
Pulsed diode forward current ^a	I _{SM}			-	-	80	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 20 A, V _{GS} = 0 V ^b		-	-	1.8	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 20A, dI/dt = 100 A/μs ^b		-	570	860	ns
Body diode reverse recovery charge	Q _{rr}			-	5.7	8.6	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

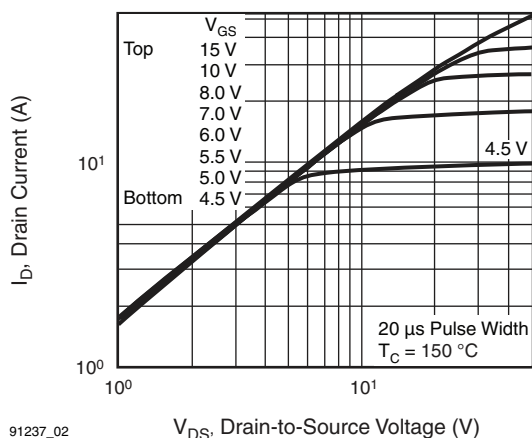
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


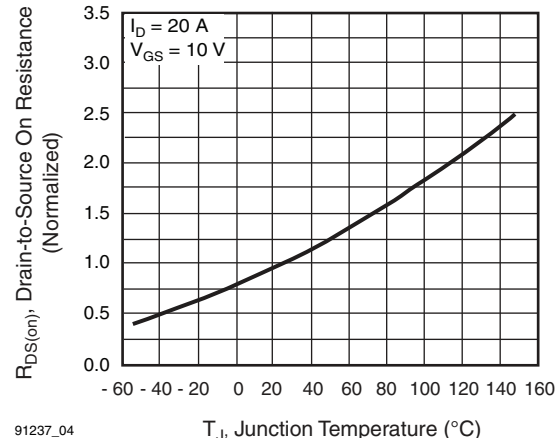
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Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$


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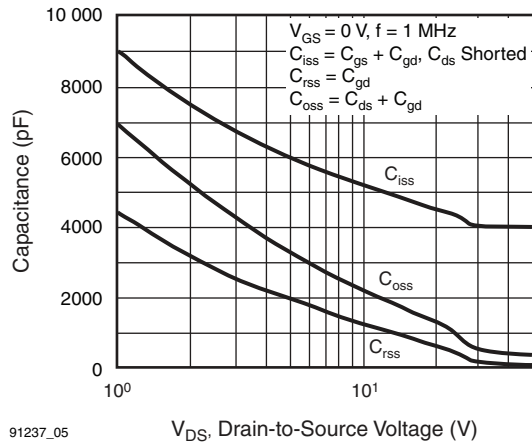
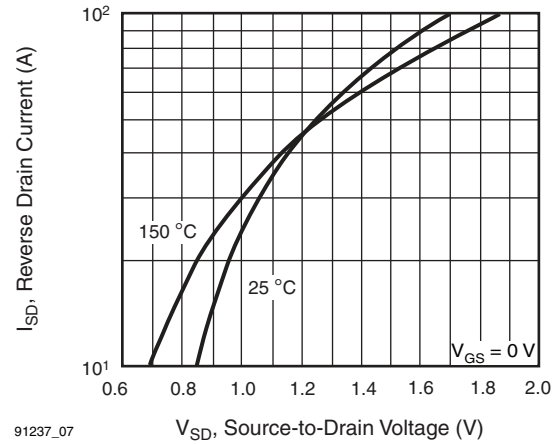
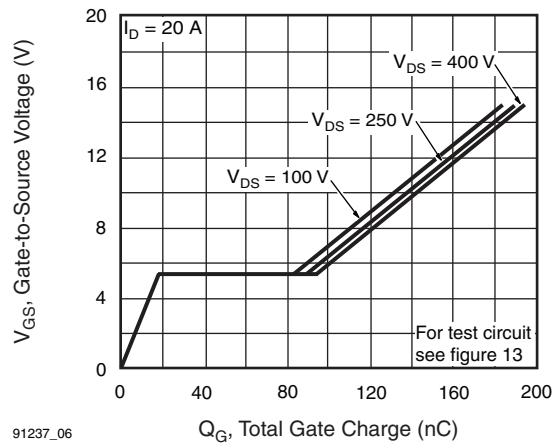
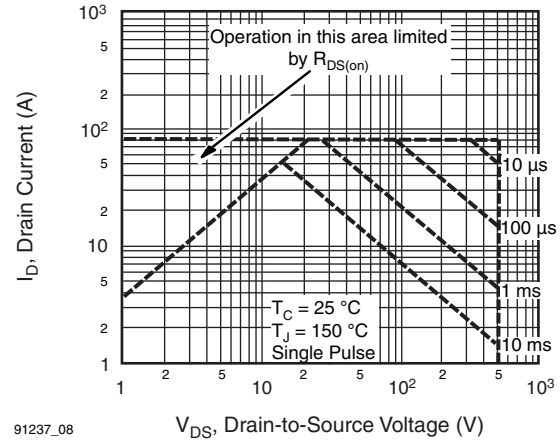
Fig. 3 - Typical Transfer Characteristics


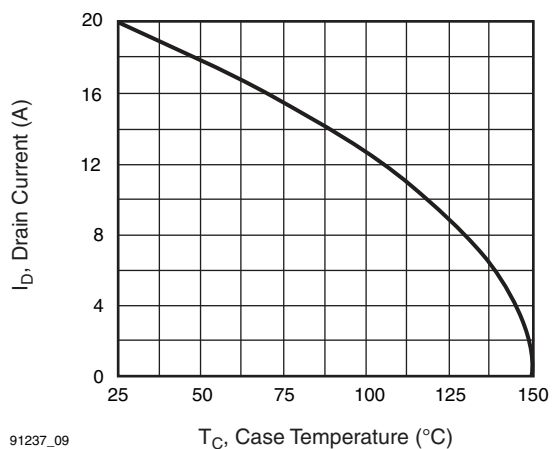
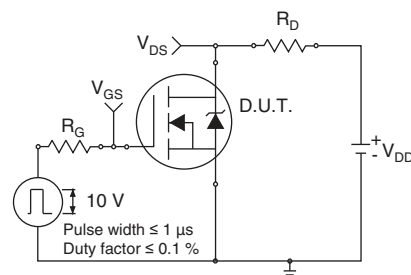
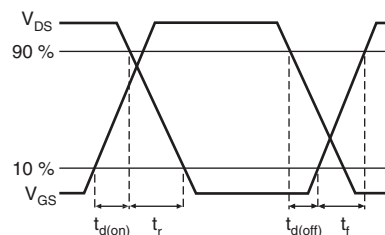
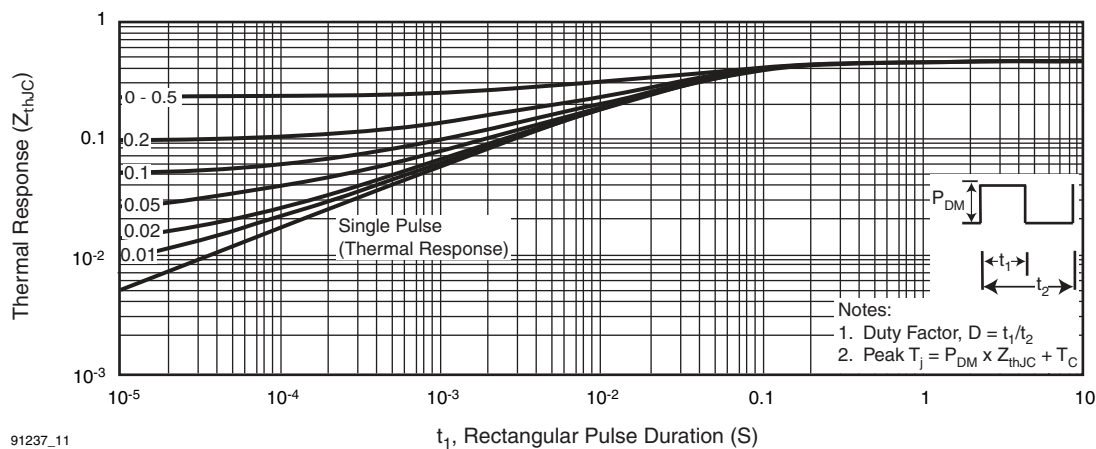
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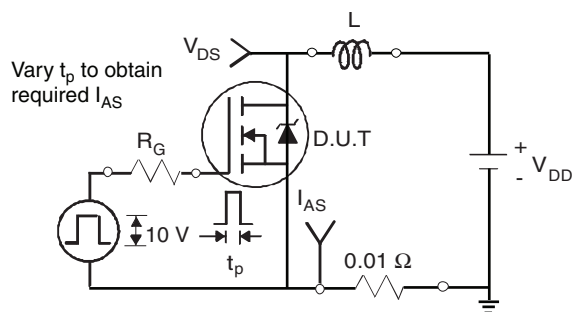
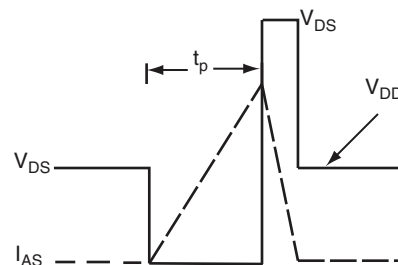
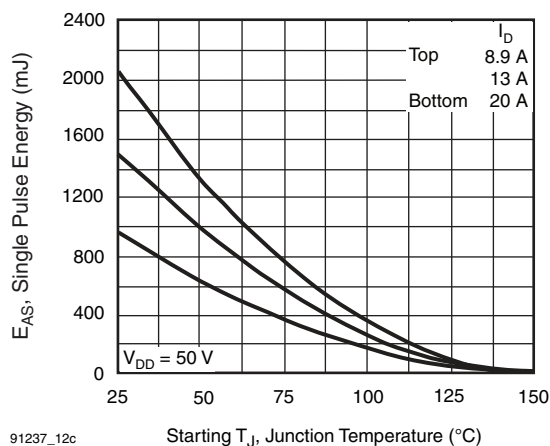
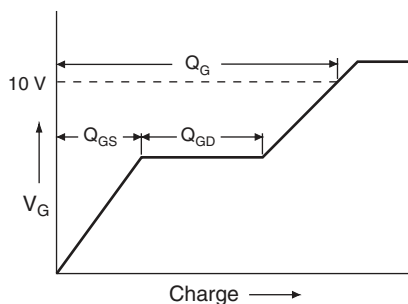
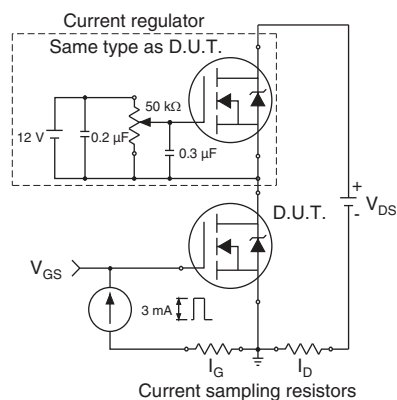
Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$


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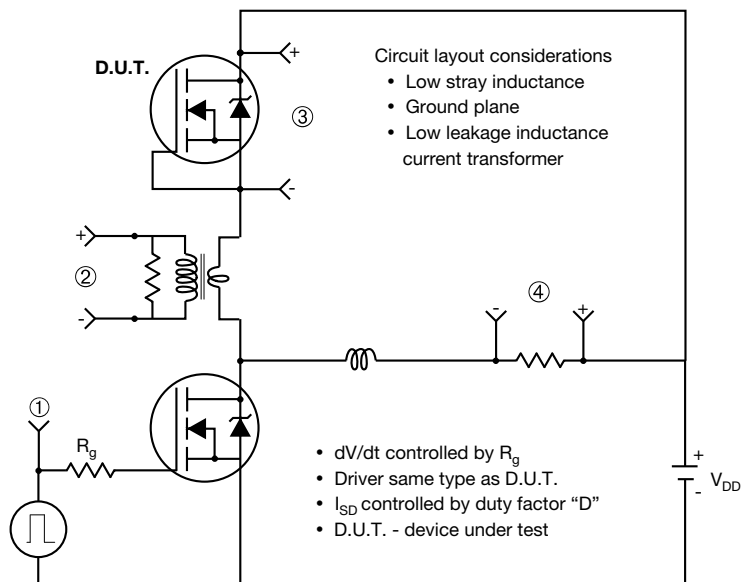
Fig. 4 - Normalized On-Resistance vs. Temperature


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10 - Switching Time Test Circuit

Fig. 11 - Switching Time Waveforms

Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 13 - Unclamped Inductive Test Circuit

Fig. 14 - Unclamped Inductive Waveforms

Fig. 15 - Maximum Avalanche Energy vs. Drain Current

Fig. 16 - Basic Gate Charge Waveform

Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

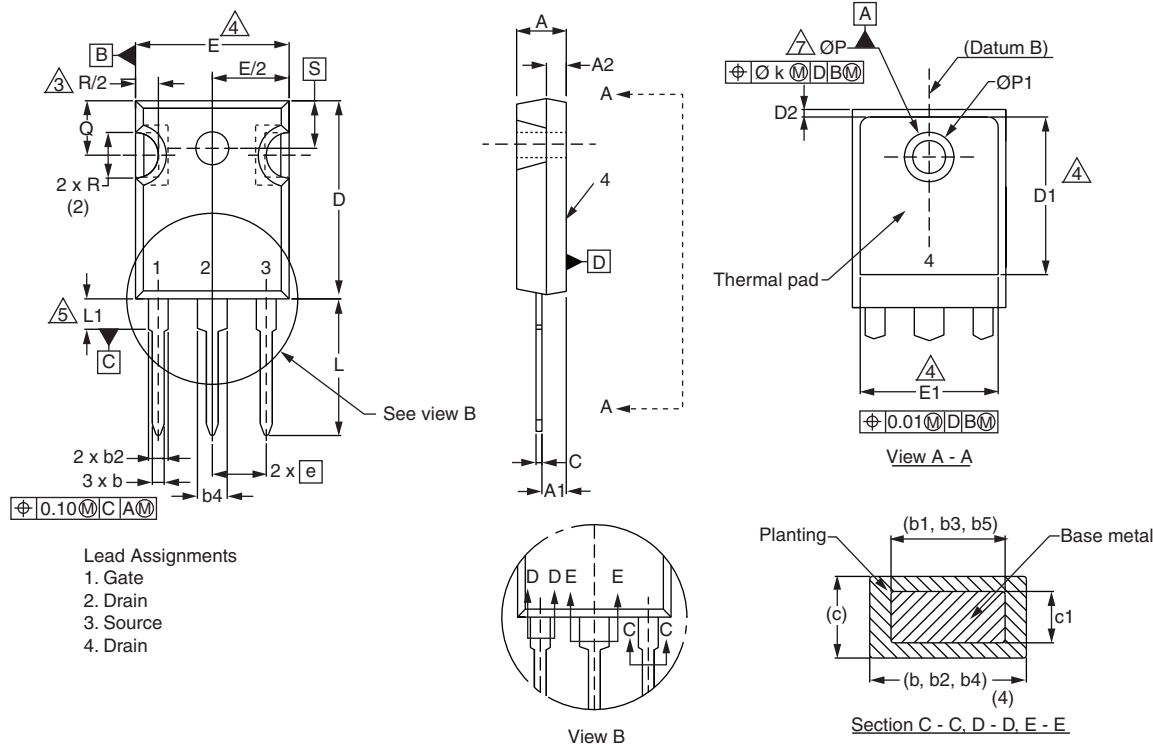
a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91237.



VERSION 2: FACILITY CODE = Y



DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

MILLIMETERS		
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

ECN: E22-0452-Rev. G, 31-Oct-2022
DWG: 5971

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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